



HPHT single crystal diamond substrate IIa type characterization for particle detectors

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In recent years, diamond detectors have been widely developed. Wide band gap (5.5 eV) and high resistivity (up to 10^{14} Ω -cm) together with high transport parameters of non-equilibrium current carrier give possibility for such detectors to be used up to a temperature – 300 °C with no serious change in their characteristics.

The paper presents the results of HPHT single-crystal diamond substrates IIa type characterization for particle detectors. The used diamond substrates [(100), with size 4×4 mm and with thickness 0.5 mm] were produced by company “New Diamond Technology”. The diamond substrates were investigated by X-ray diffraction, Fourier transform infrared spectroscopy and by atomic force microscopy. It has been shown that substrates have significant crystalline perfection. No crystallites inclusions with a different orientation were detected. At rocking curves measuring, no physical broadening was detected. The dislocation density in the current substrates is at a level below of the method sensitivity $< 10^3$ cm^{-2} . The nitrogen and boron concentrations in the substrates were estimated at 10 and 50 ppb, correspondently.

To create a test detector, contacts (3.5×3.5 mm^2) based on Pt (thickness – 150 Å) were applied to both substrate sides. Deposition was made through a metal mask using ion-plasma sputtering. At a next step, the charge transport properties were investigated by alpha spectrometry method. For this, the dependence of the charge collection efficiency versus bias voltage under irradiation with α -particles (5.499 MeV) from ^{238}Pu and different polarities of the bias voltage on the detector was measured. The obtained results were correlated with the deep centers parameters investigation by the DLTS method.

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